

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A light emitting display device comprising:

~~a gate electrode formed over a substrate having an insulating surface with a substance having a photocatalytic function therebetween;~~

a base film including a substance with a photocatalytic function formed on a substrate;

a gate electrode formed on the base film;

a gate insulating layer formed over the gate electrode;

a semiconductor layer and a first electrode formed over the gate insulating layer;

a wiring layer formed over the semiconductor layer;

a partition wall covering an edge portion of the first electrode and the wiring layer;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the wiring layer covers the edge portion of the first electrode.

2. (Currently Amended) A light emitting display device comprising:

~~a wiring layer and a first electrode formed over a substrate having an insulating surface with a substance having a photocatalytic function therebetween;~~

a base film including a substance with a photocatalytic function formed on a substrate;

a wiring layer and a first electrode formed on the base film;

a semiconductor layer formed over the wiring layer;

a gate insulating layer formed over the semiconductor layer;

a gate electrode formed over the gate insulating layer;

a partition wall covering an edge portion of the first electrode and the wiring layer;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the wiring layer covers the edge portion of the first electrode.

3. (Currently Amended) A light emitting display device comprising:

~~a gate electrode formed over a substrate having an insulating surface with a substance having a photocatalytic function therebetween;~~

a base film including a substance with a photocatalytic function formed on a substrate;

a gate electrode formed on the base film;

a gate insulating layer formed over the gate electrode;

a semiconductor layer and a first electrode formed over the gate insulating layer;

a wiring layer formed over the semiconductor layer;

a partition wall covering an edge portion of the first electrode and the wiring layer;

an electroluminescent layer over the first electrode; and a second electrode over the electroluminescent layer,

wherein the first electrode covers an edge portion of the wiring layer.

4. (Currently Amended) A light emitting display device comprising:

~~a wiring layer and a first electrode formed over a substrate having an insulating surface with a substance having a photocatalytic function therebetween;~~

a base film including a substance with a photocatalytic function formed on a substrate;

a gate electrode formed on the base film;

a semiconductor layer formed over the wiring layer;

a gate insulating layer formed over the semiconductor layer;

a gate electrode formed over the gate insulating layer;

a partition wall covering an edge portion of the first electrode and the wiring layer;

an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,

wherein the first electrode covers an edge portion of the wiring layer.

5. (Original) A light emitting display device according to any one of claims 1 to 4, wherein the substance having a photocatalytic function comprises titanium oxide.

6. (Currently Amended) A light emitting display device comprising:

a conductive layer including a refractory metal over a substrate having an insulating surface;

- a gate electrode formed over the conductive layer;
- a gate insulating layer formed over the gate electrode;
- a semiconductor layer and a first electrode formed over the gate insulating layer;
- a wiring layer formed over the semiconductor layer;
- a partition wall covering an edge portion of the first electrode and the wiring layer;
- an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,

wherein the wiring layer covers the edge portion of the first electrode.

7. (Original) A light emitting display device comprising:

a conductive layer including a refractory metal over a substrate having an insulating surface;

- a wiring layer and a first electrode formed over the conductive layer;
- a semiconductor layer formed over the wiring layer;
- a gate insulating layer formed over the semiconductor layer; a gate electrode formed over the gate insulating layer;
- a partition wall covering an edge portion of the first electrode and the wiring layer;
- an electroluminescent layer over the first electrode; and
- a second electrode over the electroluminescent layer,

wherein the wiring layer covers the edge portion of the first electrode.

8. (Original) A light emitting display device comprising:

a conductive layer including a refractory metal over a substrate having an insulating surface;

- a gate electrode formed over the conductive layer;
- a gate insulating layer formed over the gate electrode;
- a semiconductor layer and a first electrode formed over the gate insulating layer;
- a wiring layer formed over the semiconductor layer;
- a partition wall covering an edge portion of the first electrode and the wiring layer;
- an electroluminescent layer over the first electrode; and

a second electrode over the electroluminescent layer,
wherein the first electrode covers an edge portion of the wiring layer.

9. (Original) A light emitting display device comprising:
a conductive layer including a refractory metal over a substrate having an insulating surface;
a wiring layer and a first electrode formed over the conductive layer;
a semiconductor layer formed over the wiring layer;
a gate insulating layer formed over the semiconductor layer;
a gate electrode formed over the gate insulating layer;
a partition wall covering an edge portion of the first electrode and the wiring layer;
an electroluminescent layer over the first electrode; and
a second electrode over the electroluminescent layer,
wherein the first electrode covers an edge portion of the wiring layer.

10. (Original) A light emitting display device according to any one of claims 6 to 9, wherein the refractory metal is selected from the group consisting of Ti (titanium), W (tungsten), Cr (chromium), Al (aluminum), Ta (tantalum), Ni (nickel), Zr (zirconium), Hf (hafnium), V (vanadium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Co (cobalt), and Rh (rhodium).

11. (Currently Amended) A light emitting display device according to any one of claims 1 [[-]] to 4 and 6 [[-]] to 9, wherein the gate electrode and the wiring layer are made of a material selected from the group consisting of silver, gold, copper, and indium tin oxide.

12. (Currently Amended) A light emitting display device according to any one of claims 1 [[-]] to 4 and 6 [[-]] to 9, wherein the semiconductor layer is a semi-amorphous semiconductor containing hydrogen and halogen and having a crystal structure.

13. (Currently Amended) A TV set including a display screen having the light emitting display device according to any one of claims 1[[-]] to 4 and 6 [[-]] to 9.

14. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

~~forming a gate electrode over a substrate having an insulating surface with a substance having a photocatalytic function therebetween by a droplet discharge method;~~

forming a base film including a substance with a photocatalytic function on a substrate;

forming a gate electrode on the base film having an insulating surface by a droplet discharge method;

forming a gate insulating layer over the gate electrode;

forming a semiconductor layer over the gate insulating layer;

forming a first electrode over the gate insulating layer by a droplet discharge method;

forming a wiring layer over the semiconductor layer by a droplet discharge method to cover an edge of the first electrode;

forming a partition wall to cover the edge portion of the first electrode and the wiring layer;

forming an electroluminescent layer over the first electrode; and

forming a second electrode over the electroluminescent layer by a droplet discharge method.

15. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

~~forming a first electrode over a substrate having an insulating surface with a substance having a photocatalytic function therebetween by a droplet discharge method;~~

forming a base film including a substance with a photocatalytic function on a substrate;

forming a gate electrode on the base film having an insulating surface by a droplet discharge method;

forming a wiring layer over the substrate having an insulating surface with a substance having a photocatalytic function therebetween to cover an edge portion of the first electrode;

forming a semiconductor layer over the wiring layer;

forming a gate insulating layer over the semiconductor layer;
forming a gate electrode over the gate insulating layer by a droplet discharge method;
forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a droplet discharge method.

16. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

~~forming a gate electrode over a substrate having an insulating surface with a substance having a photocatalytic function therebetween by a droplet discharge method;~~

~~forming a base film including a substance with a photocatalytic function on a substrate;~~

~~forming a gate electrode on the base film having an insulating surface by a droplet discharge method;~~

forming a gate insulating layer over the gate electrode;

forming a semiconductor layer over the gate insulating layer;

forming a wiring layer over the semiconductor layer by a droplet discharge method;

forming a first electrode over the gate insulating layer by a droplet discharge method to cover an edge portion of the wiring layer;

forming a partition wall to cover an edge portion of the first electrode and the wiring layer;

forming an electroluminescent layer over the first electrode; and

forming a second electrode over the electroluminescent layer by a droplet discharge method.

17. (Currently Amended) A method for manufacturing a light emitting display device, comprising:

~~forming a wiring layer over a substrate having an insulating surface with a substance having a photocatalytic function therebetween by a droplet discharge method;~~

~~forming a first electrode over the substrate having an insulating surface with a substance having a photocatalytic function therebetween by a droplet discharge method to cover an edge portion of the wiring layer;~~

~~forming a base film including a substance with a photocatalytic function on a substrate;~~

~~forming a wiring layer on the base film having an insulating surface by a droplet discharge method;~~

~~forming a first electrode on the base film having an insulating surface by a droplet discharge method to cover an edge portion of the wiring layer;~~

forming a semiconductor layer over the wiring layer;

forming a gate insulating layer over the semiconductor layer;

forming a gate electrode over the gate insulating layer by a droplet discharge method;

forming a partition wall to cover an edge portion of the first electrode and the wiring layer;

forming an electroluminescent layer over the first electrode; and

forming a second electrode over the electroluminescent layer by a droplet discharge method.

18. (Original) A method for manufacturing a light emitting display device according to any one of claims 14 to 17, wherein titanium oxide is used as the substance having a photocatalytic function.

19. (Original) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;

forming a gate electrode over the conductive layer by a droplet discharge method;

forming a gate insulating layer over the gate electrode;

forming a semiconductor layer over the gate insulating layer;

forming a first electrode over the gate insulating layer by a droplet discharge method;
forming a wiring layer over the semiconductor layer by a droplet discharge method to cover an edge portion of the first electrode;
forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a droplet discharge method.

20. (Original) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;
forming a first electrode over the conductive layer by a droplet discharge method;
forming a wiring layer over the conductive layer by a droplet discharge method to cover an edge portion of the first electrode;
forming a semiconductor layer over the wiring layer;
forming a gate insulating layer over the semiconductor layer;
forming a gate electrode over the gate insulating layer by a droplet discharge method;
forming a partition wall to cover the edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a droplet discharge method.

21. (Original) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;
forming a gate electrode over the conductive layer by a droplet discharge method;

forming a gate insulating layer over the gate electrode;
forming a semiconductor layer over the gate insulating layer;
forming a wiring layer over the semiconductor layer by a droplet discharge method;
forming a first electrode over the gate insulating layer by a droplet discharge method to cover an edge portion of the wiring layer;
forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a droplet discharge method.

22. (Original) A method for manufacturing a light emitting display device, comprising:

forming a conductive layer including a refractory metal over a substrate having an insulating surface;
forming a wiring layer over the conductive layer by a droplet discharge method;
forming a first electrode over the conductive layer by a droplet discharge method to cover an edge portion of the wiring layer;
forming a semiconductor layer over the wiring layer;
forming a gate insulating layer over the semiconductor layer;
forming a gate electrode over the gate insulating layer by a droplet discharge method;
forming a partition wall to cover an edge portion of the first electrode and the wiring layer;
forming an electroluminescent layer over the first electrode; and
forming a second electrode over the electroluminescent layer by a droplet discharge method.

23. (Original) A method for manufacturing a light emitting display device according to any one of claims 19 to 22,

wherein the refractory metal is selected from the group consisting of Ti (titanium), W (tungsten), Cr (chromium), Al (aluminum), Ta (tantalum), Ni (nickel), Zr (zirconium), Hf

(hafnium), V (vanadium), Ir (iridium), Nb (niobium), Pd (lead), Pt (platinum), Mo (molybdenum), Co (cobalt), and Rh (rhodium).

24. (Currently Amended) A method for manufacturing a light emitting display device according to any_one of claims 14 ~~[-]~~ to 17, 19 ~~[-]~~ to 21, and 22,

wherein the gate electrode and the wiring layer comprise a material selected from the group consisting of silver, gold, copper, and indium tin oxide.

25. (Currently Amended) A method for manufacturing a light emitting display device according to any_one of claims 14 ~~[-]~~ to 17, 19 ~~[-]~~ to 21, and 22,

wherein the semiconductor layer comprises a semi-amorphous semiconductor containing hydrogen and halogen and having a crystal structure.